

DESCRIPTION

A1368 is a silicon PNP epitaxial type transistor. It designed with high collector dissipation, high voltage.
Complementary with 2SC3438.

FEATURE

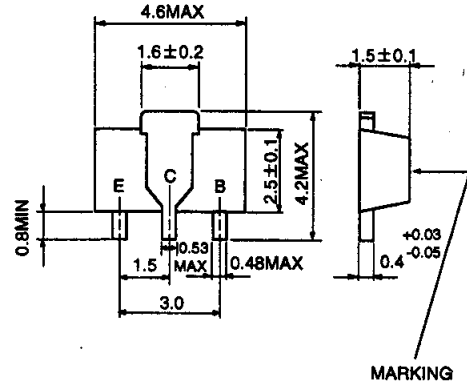
- High voltage $V_{CE0} = -100V$
- High collector current ($I_{CM} = -800mA$)
- High gain band width product $f_r = 130MHz$ typ
- High collector dissipation $P_c = 500mW$
- Small package for mounting

APPLICATION

Relay drive power supply etc.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

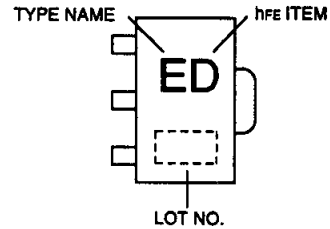
E : EMITTER
C : COLLECTOR EIAJ : SC-62
B : BASE JEDEC : -

Note)
The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V _{CB0}	Collector to Base voltage	-100	V
V _{EB0}	Emitter to Base voltage	-5	V
V _{CE0}	Collector to Emitter voltage	-100	V
I _{CM}	Peak Collector current	-800	mA
I _C	Collector current	-500	mA
P _C	Collector dissipation(Ta=25°C)	500	mW
T _J	Junction temperature	+150	°C
T _{stg}	Storage temperature	-55 to +150	°C

MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

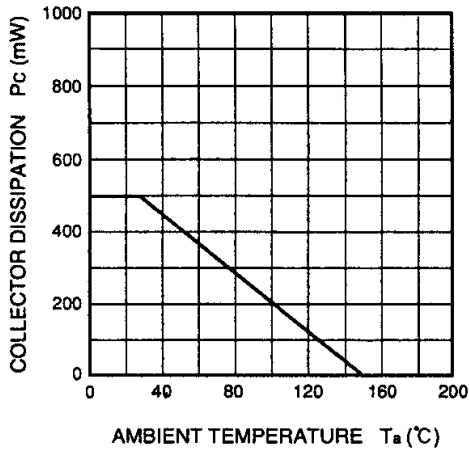
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{(BR)CB0}	C to B break down voltage	I _C =-10 μA, I _E =0	-100			V
V _{(BR)EB0}	E to B break down voltage	I _E =-10 μA, I _C =0	-5			V
V _{(BR)CE0}	C to E break down voltage	I _C =-1mA, R _{BE} =∞	-100			V
I _{CB0}	Collector cut off current	V _{CB} =-50V, I _E =0			-0.5	μA
I _{EB0}	Emitter cut off current	V _{EB} =-2V, I _C =0			-0.5	μA
hFE *	DC forward current gain	V _{CE} =-10V, I _C =-10mA	55		300	—
V _{CE(sat)}	C to E saturation voltage	I _C =-150mA, I _B =-15mA		-0.15	-0.5	V
f _T	Gain band width product	V _{CE} =-10V, I _E =10mA		130		MHz
C _{ob}	Collector output capacitance	V _{CB} =-10V, I _E =0, f=1MHz		11		pF

* : It shows hFE classification in right table.

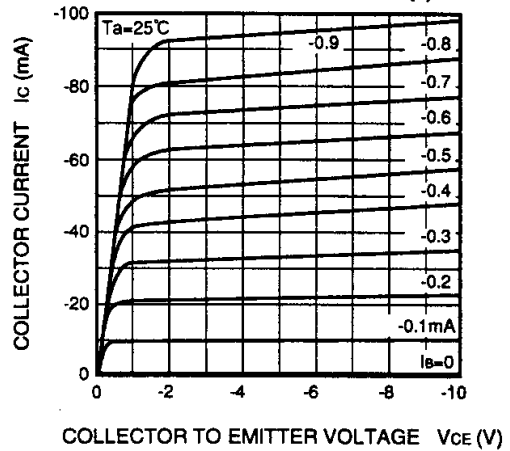
Marking	EC	ED	EE
hFE	55 to 110	90 to 180	150 to 300

TYPICAL CHARACTERISTICS

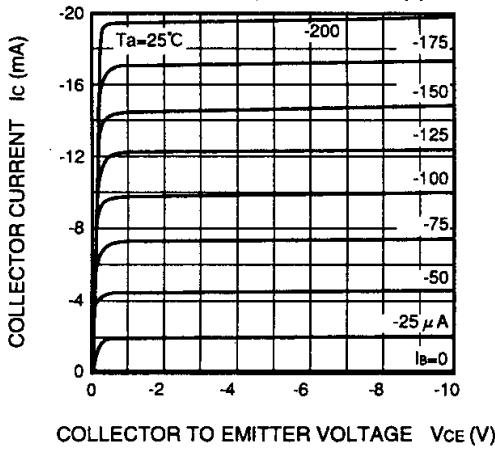
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



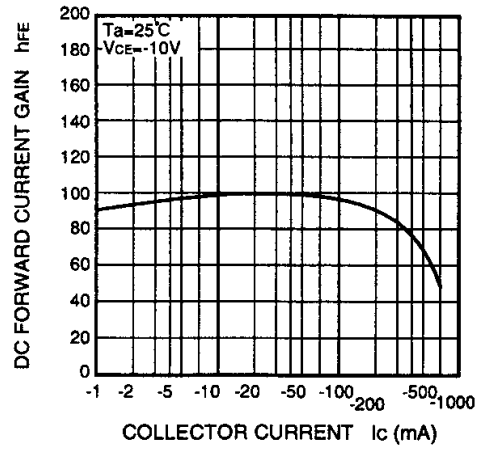
COMMON EMITTER OUTPUT (1)



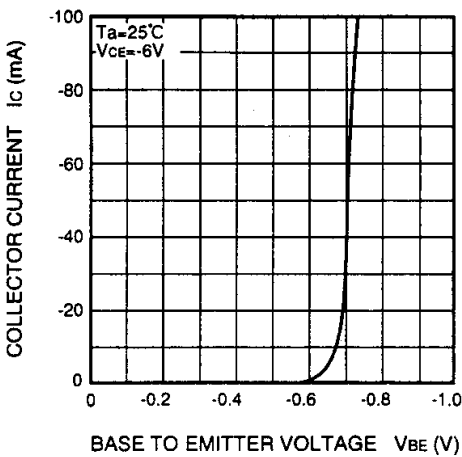
COMMON EMITTER OUTPUT (2)



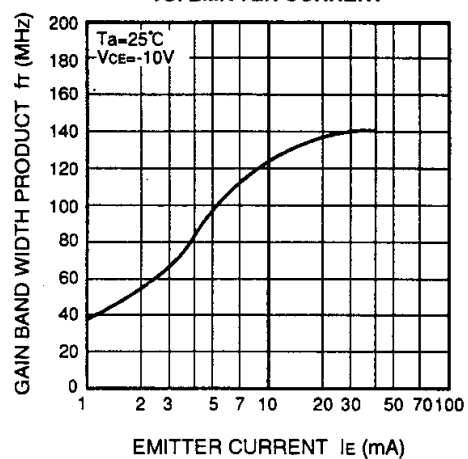
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT

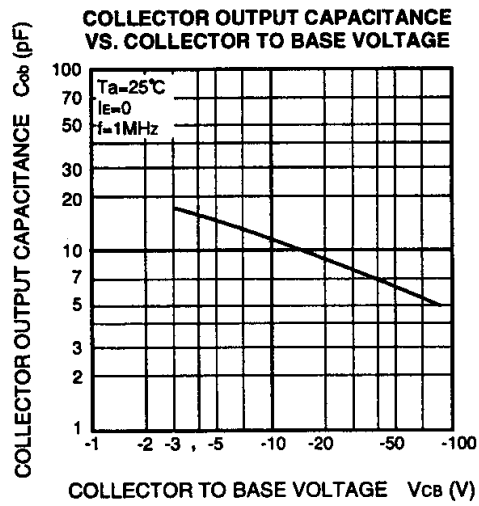


COMMON EMITTER TRANSFER



GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT





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